Silicon PIN diode
Rev. 01 - 27 May 2004
Preliminary data sheet

## 1. Product profile

### 1.1 General description

Planar PIN diode in a SOD882 ultra small SMD plastic package.

### 1.2 Features

- High voltage, current controlled RF resistor

■ Low losses at very low currents

- Low diode capacitance
- Very low series inductance
- For applications up to 3 GHz .


### 1.3 Applications

- RF attenuators and switches.


## 2. Pinning information


[1] Package marked by a masking bar.

## 3. Ordering information

Table 2: Ordering information

| Type number | Package |  |  |
| :--- | :--- | :--- | :--- |
|  | Name | Description | Version |
| BAP142L | - | Leadless ultra small plastic package; 2 terminals; <br> body $1.0 \times 0.6 \times 0.5 \mathrm{~mm}$ | SOD882 |

## 4. Marking

Table 3: Marking

| Type number | Marking code |
| :--- | :--- |
| BAP142L | E1 |

## 5. Limiting values

Table 4: Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
| :--- | :--- | :--- | :--- | :--- | :--- |
| $\mathrm{V}_{\mathrm{R}}$ | continuous reverse voltage |  | - | 50 | V |
| $\mathrm{I}_{\mathrm{F}}$ | continuous forward current |  | - | 100 | mA |
| $\mathrm{P}_{\text {tot }}$ | total power dissipation | $\mathrm{T}_{\mathrm{S}}=90^{\circ} \mathrm{C}$ | - | 315 | mW |
| $\mathrm{~T}_{\text {stg }}$ | storage temperature |  | -65 | +150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{j}}$ | junction temperature |  | -65 | +150 | ${ }^{\circ} \mathrm{C}$ |

## 6. Thermal characteristics

Table 5: Thermal characteristics

| Symbol | Parameter | Conditions | Typ | Unit |
| :--- | :--- | :--- | :--- | :--- |
| $\mathrm{R}_{\text {th( }(-\mathrm{s})}$ | thermal resistance from junction |  | 190 | K/W |
|  | to soldering point |  |  |  |

## 7. Characteristics

Table 6: Electrical characteristics
$T_{j}=25^{\circ} \mathrm{C}$ unless otherwise specified.

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $V_{F}$ | forward voltage | $\mathrm{I}_{\mathrm{F}}=50 \mathrm{~mA}$ | - | 0.95 | 1.1 | V |
| $\mathrm{I}_{\mathrm{R}}$ | reverse current | $\mathrm{V}_{\mathrm{R}}=50 \mathrm{~V}$ | - | - | 100 | nA |
|  |  | $\mathrm{V}_{\mathrm{R}}=20 \mathrm{~V}$ | - | - | 20 | nA |
| $\mathrm{C}_{\mathrm{d}}$ | diode capacitance | $\mathrm{f}=1 \mathrm{MHz}$; see $\underline{\text { Figure } 2}$ |  |  |  |  |
|  |  | $\mathrm{V}_{\mathrm{R}}=0 \mathrm{~V}$ | - | 0.26 | - | pF |
|  |  | $\mathrm{V}_{\mathrm{R}}=1 \mathrm{~V}$ | - | 0.23 | 0.35 | pF |
|  |  | $\mathrm{V}_{\mathrm{R}}=20 \mathrm{~V}$ | - | 0.17 | 0.25 | pF |
| $r_{\text {D }}$ | diode forward resistance | $f=100 \mathrm{MHz}$; see Figure 1 |  |  |  |  |
|  |  | $\mathrm{I}_{\mathrm{F}}=0.5 \mathrm{~mA}$ | - | 3.3 | 5.0 | $\Omega$ |
|  |  | $\mathrm{I}_{\mathrm{F}}=1 \mathrm{~mA}$ | - | 2.4 | 3.6 | $\Omega$ |
|  |  | $\mathrm{I}_{\mathrm{F}}=10 \mathrm{~mA}$ | - | 1.0 | 1.5 | $\Omega$ |
|  |  | $\mathrm{I}_{\mathrm{F}}=100 \mathrm{~mA}$ | - | 0.6 | 0.9 | $\Omega$ |

Table 6: Electrical characteristics ...continued $T_{j}=25^{\circ} \mathrm{C}$ unless otherwise specified.

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\left\|s_{21}\right\|^{2}$ | isolation | $\mathrm{V}_{\mathrm{R}}=0 \mathrm{~V}$; see Figure 4 |  |  |  |  |
|  |  | $\mathrm{f}=900 \mathrm{MHz}$ | - | 16.0 | - | dB |
|  |  | $\mathrm{f}=1800 \mathrm{MHz}$ | - | 11.6 | - | dB |
|  |  | $\mathrm{f}=2450 \mathrm{MHz}$ | - | 9.9 | - | dB |
| $\overline{\left\|s_{21}\right\|^{2}}$ | insertion loss | $\mathrm{I}_{\mathrm{F}}=0.5 \mathrm{~mA}$; see Figure 3 |  |  |  |  |
|  |  | $\mathrm{f}=900 \mathrm{MHz}$ | - | 0.24 | - | dB |
|  |  | $\mathrm{f}=1800 \mathrm{MHz}$ | - | 0.25 | - | dB |
|  |  | $\mathrm{f}=2450 \mathrm{MHz}$ | - | 0.26 | - | dB |
| $\left\|s_{21}\right\|^{2}$ | insertion loss | $\mathrm{I}_{\mathrm{F}}=1 \mathrm{~mA}$; see Figure 3 |  |  |  |  |
|  |  | $\mathrm{f}=900 \mathrm{MHz}$ | - | 0.18 | - | dB |
|  |  | $\mathrm{f}=1800 \mathrm{MHz}$ | - | 0.19 | - | dB |
|  |  | $\mathrm{f}=2450 \mathrm{MHz}$ | - | 0.21 | - | dB |
| $\left\|s_{21}\right\|^{2}$ | insertion loss | $\mathrm{I}_{\mathrm{F}}=10 \mathrm{~mA}$; see $\underline{\text { Figure 3 }}$ |  |  |  |  |
|  |  | $\mathrm{f}=900 \mathrm{MHz}$ | - | 0.10 | - | dB |
|  |  | $\mathrm{f}=1800 \mathrm{MHz}$ | - | 0.11 | - | dB |
|  |  | $\mathrm{f}=2450 \mathrm{MHz}$ | - | 0.14 | - | dB |
| $\overline{\left\|s_{21}\right\|^{2}}$ | insertion loss | $\mathrm{I}_{\mathrm{F}}=100 \mathrm{~mA}$; see Figure 3 |  |  |  |  |
|  |  | $\mathrm{f}=900 \mathrm{MHz}$ | - | 0.07 | - | dB |
|  |  | $\mathrm{f}=1800 \mathrm{MHz}$ | - | 0.09 | - | dB |
|  |  | $\mathrm{f}=2450 \mathrm{MHz}$ | - | 0.11 | - | dB |
| $\tau_{\mathrm{L}}$ | charge carrier life time | when switched from $\begin{aligned} & \mathrm{I}_{\mathrm{F}}=10 \mathrm{~mA} \text { to } \mathrm{I}_{\mathrm{R}}=6 \mathrm{~mA} ; \\ & \mathrm{R}_{\mathrm{L}}=100 \Omega ; \\ & \text { measured at } \mathrm{I}_{\mathrm{R}}=3 \mathrm{~mA} \end{aligned}$ | - | 0.12 | - | $\mu \mathrm{s}$ |
| LS | series inductance | $\mathrm{I}_{\mathrm{F}}=100 \mathrm{~mA} ; \mathrm{f}=100 \mathrm{MHz}$ | - | 0.6 | - | nH |



Fig 1. Forward resistance as a function of forward current; typical values.

(1) $I_{F}=100 \mathrm{~mA}$.
(2) $I_{F}=10 \mathrm{~mA}$.
(3) $\mathrm{I}_{\mathrm{F}}=1 \mathrm{~mA}$.
(4) $\mathrm{I}_{\mathrm{F}}=0.5 \mathrm{~mA}$.

Diode inserted in series with a $50 \Omega$ stripline circuit and biased via the analyzer Tee network; $\mathrm{T}_{\mathrm{amb}}=25^{\circ} \mathrm{C}$.

Fig 3. Insertion loss $\left(\left.\left|\mathbf{S}_{21}\right|\right|^{2}\right)$ of the diode as a function of frequency; typical values.


Fig 2. Diode capacitance as a function of reverse voltage; typical values.


Diode zero biased and inserted in a $50 \Omega$ microstrip circuit; $\mathrm{T}_{\mathrm{amb}}=25^{\circ} \mathrm{C}$.

Fig 4. Isolation $\left(\left|\mathbf{s}_{21}\right|^{2}\right)$ of the diode as a function of frequency; typical values.

## 8. Package outline



Fig 5. Package outline.

## 9. Revision history

Table 7: Revision history

| Document ID | Release date | Data sheet status | Change notice | Order number | Supersedes |
| :--- | :--- | :--- | :--- | :--- | :--- | :--- |
| BAP142L_1 | 20040527 | Preliminary data | - | 939775013056 | - |

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| Level | Data sheet status $[1]$ | Product status $\underline{[2]}[3]$ | Definition <br> I |
| :--- | :--- | :--- | :--- |
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## 13. Contact information

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